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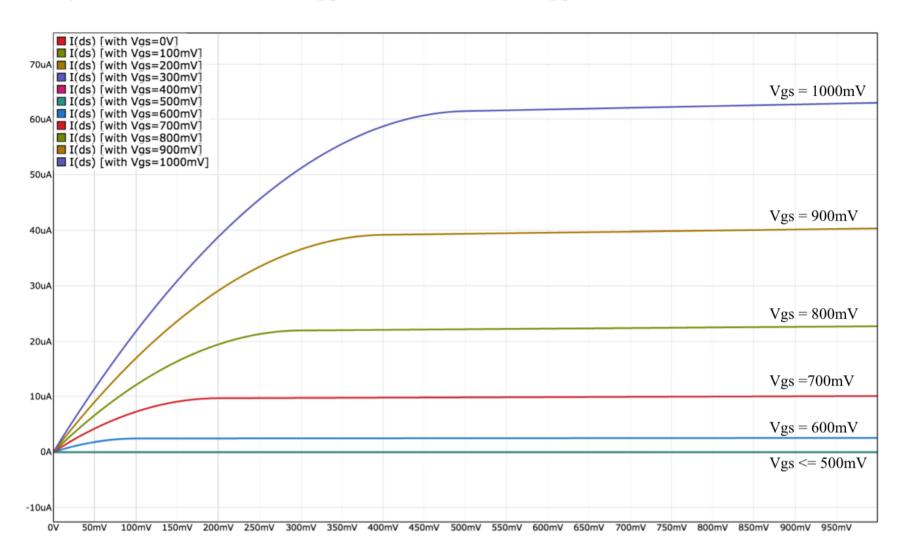
⊞ Calculator

LE3.1.1: MOSFET Measurements

3/3 points (ungraded)

Here's the figure from the last video showing I_{DS} as a function of V_{GS} and V_{DS} . The threshold voltage, V_{TH} , of the MOSFET is 0.5V. The measurements were taken using an n-channel MOSFET with a width of 4 and a length of 1, expressed as multiples of the minimum feature size for a particular manufacturing process.

In the graph below, the vertical axis is I_{DS} and the horizontal axis is V_{DS} .



Please use the plots to answer the following questions.

(A) If $V_S=.1V, V_D=0.5V$ and $V_G=0.8V$, how much current will flow through the MOSFET switch, i.e., what is I_{DS} ? Note that the units are in μA .

 I_{DS} (in μA , $\pm 10\%$): 10

(B) Using the topmost curve in the figure, we see that when $V_{GS}=1V$ and $V_{DS}=.15V$, $I_{DS}=30\mu A$. Please compute the effective resistance $R_{\rm eff}$ using Ohm's Law, which tells us $V_{DS}=I_{DS}R_{\rm eff}$.

 $R_{
m eff}$ (in Ohms, $\pm 10\%$): 5000

(C) If we changed the width of the MOSFET from 4 to 6 and remeasured I_{DS} when $V_{GS}=1V$ and $V_{DS}=.15V$, give an approximate value for the new I_{DS} measurement. Hint: $I_{DS}\propto W/L$.

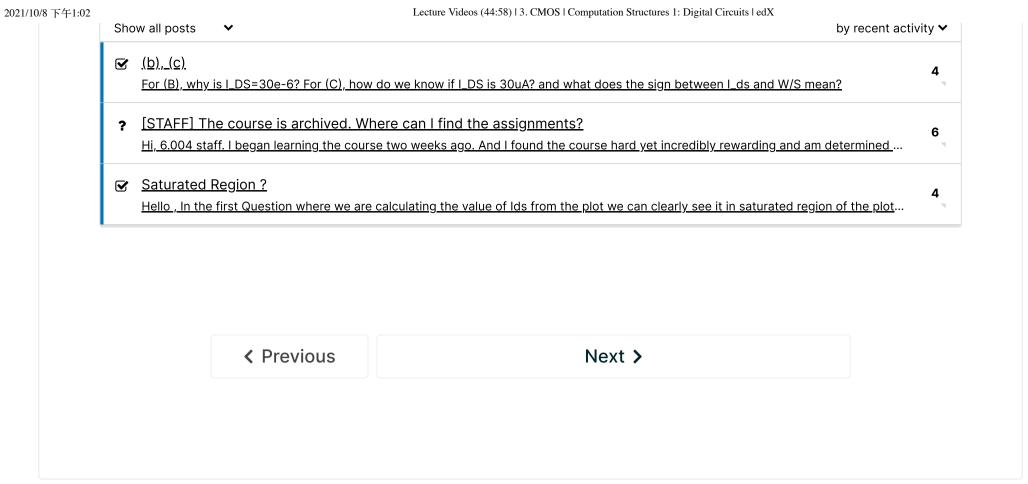
 I_{DS} (in μA , $\pm 10\%$): 45

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